

**Silicon PNP Power Transistor**

**2SB772**

**DESCRIPTION**

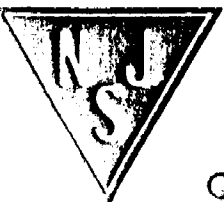
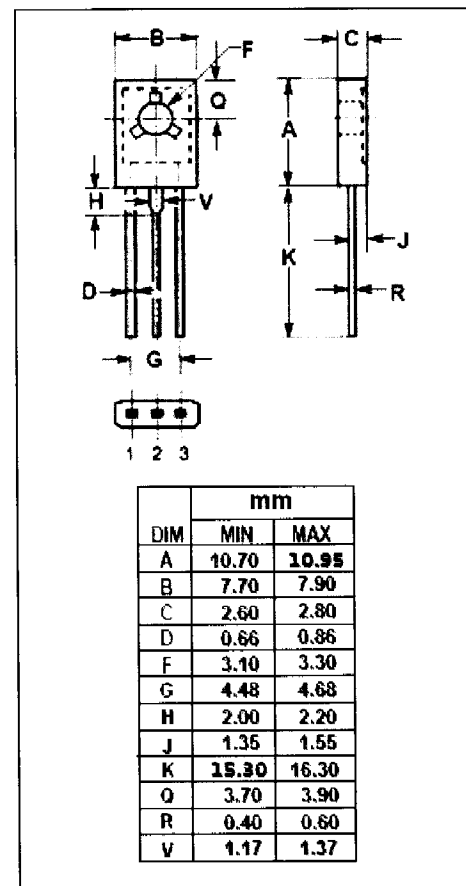
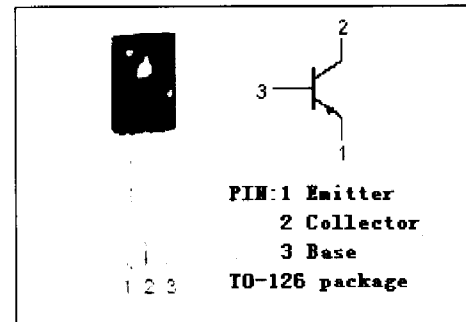
- High Collector Current  $-I_C = -3A$
- High Collector-Emitter Breakdown Voltage:  
 $V_{(BR)CEO} = -30V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Low Saturation Voltage
- Complement to Type 2SD882

**APPLICATIONS**

- Designed for use in the output stage of 3 watts audio amplifier, voltage regulator, DC-DC converter and relay driver.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-3	A
$I_{CP}$	Collector Current-Pulse	-7	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	10	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2A; I_B = -0.2A$			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -2A; I_B = -0.2A$			-2.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -30V; I_E = 0$			-1.0	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -3V; I_C = 0$			-1.0	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C = -20mA; V_{CE} = -2V$	30			
$h_{FE-2}$	DC Current Gain	$I_C = -1A; V_{CE} = -2V$	60		400	
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.1A; V_{CE} = -5V$		80		MHz
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10V, f_{test} = 1\text{MHz}$		55		pF

### ◆ $h_{FE-2}$ Classifications

R	Q	P	E
60-120	100-200	160-320	200-400